ELECTRONICS, INC.
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NTE5800 thru NTE5809
Axial Lead Standard Recovery
Silicon Rectifiers, 3 Amp

Description:

The NTE5800 through NTE5809 silicon rectifiers are designed for use in power supplies and other applications having need of a device with the following features:

- High Current to Small Size
- High Surge Current Capability
- Low Forward Voltage Drop

Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}
Working Peak Reverse Voltage, V_{RWM}
DC Blocking Voltage, V_R

NTE5800	50V
NTE5801	100V
NTE5802	200V
NTE5803	300V
NTE5804	400V
NTE5805	500V
NTE5806	600V
NTE5808	800V
NTE5809	1000V

Non–Repetitive Peak Reverse Voltage, V_{RSM}

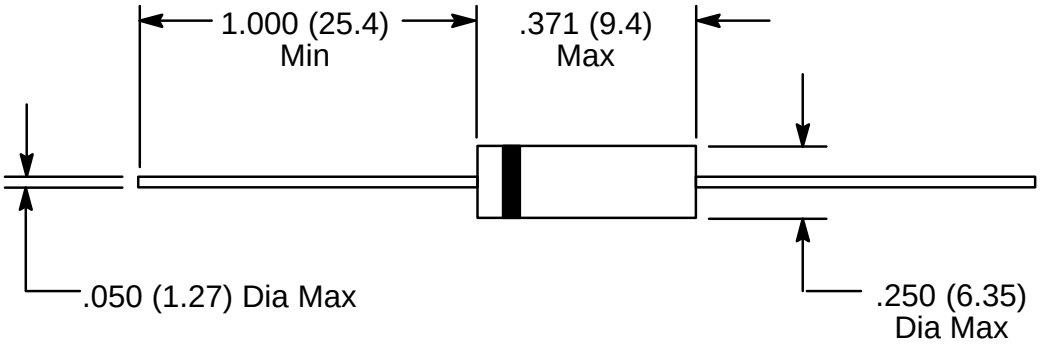
NTE5800	100V
NTE5801	200V
NTE5802	400V
NTE5803	425V
NTE5804	525V
NTE5805	625V
NTE5806	800V
NTE5808	1000V
NTE5809	1200V

Average Rectified Forward Current, I_O
(Single Phase Resistive Load, 1/2” Leads, T_L = +105°C) 3A
Non–Repetitive Peak Surge Current, I_{FSM}
(Surge Applied at Rated Load Conditions, One Cycle) 200A
Operating Junction Temperature Range, T_J . . . . . –65° to +175°C
Storage Junction Temperature Range, T_{stg} . . . . . –65° to +175°C
Thermal Resistance, Junction–to–Ambient (PC Board Mount, 1/2” Leads), R_{thJA} . . . . . +53°C/W

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	v_F	i_F = 9.4A, Note 1	–	–	1.2	V
Average Reverse Current	$I_{R(AV)}$	Note 1	–	–	500	μA
DC Reverse Current	I_R	Rated DC Voltage, T_L = 150°C	–	–	500	μA

Note 1. Measured in a single–phase half–wave circuit and operated at rated load conditions: T_L = 105°C. I_O = 3A. $V_r = V_{RWM}$.



Color Band Denotes Cathode